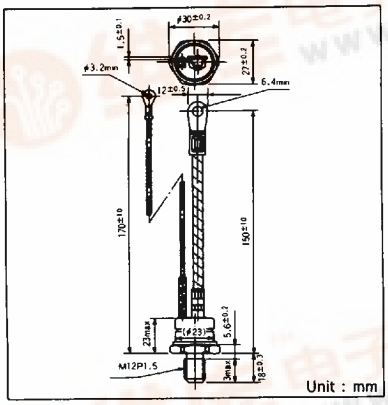
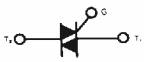
TRIAC
SSG100C

For general A.C. power control applications such as A.C. switches, light controls, speed controls and heater controls etc.

- General A.C. power use
- $I_{T(RMS)}$ = 100A
- High voltage up to 1200V
- High surge current of 1200A
- Package types;stud





■Maximum Ratings

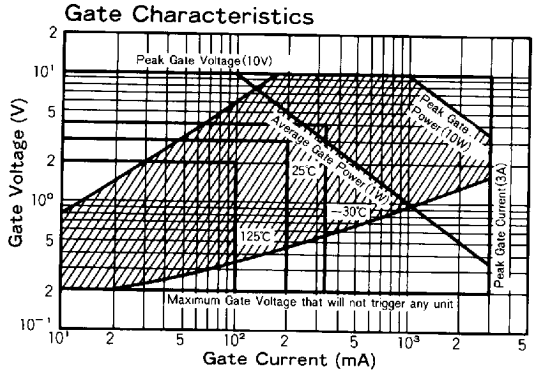
Symbol	Item	SSG100C40	SSG100C60	SSG100C80	SSG100C100	SSG100C120	Unit
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	800	1000	1200	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S On-State Current	Tc = 83°C	100	A
I_{TSM}	Surge On-State Current	One cycle, 50/60Hz, peak, non-repetitive	1080/1200	A
I^2t	I^2t	Value for one cycle of surge current	6000	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I_G = 200mA, Tj = 25°C, V_D = 1/2 V_{DRM}, dI_G/dt = 1A/μs	50	A/μs
Tj	Operating Junction Temperature		−30～+125	°C
Tstg	Storage Temperature		−30～+125	°C
	Mounting Torque	Recommended Value 112kgf•cm	140	kgf•cm
	Mass	Excluding nut & washer. 12.5g. and wrapping material 22.6g	96	g

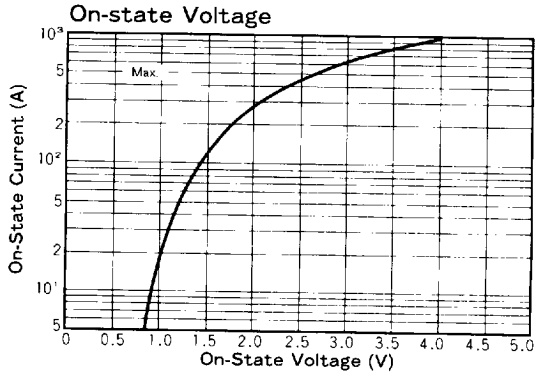
■Electrical Characteristics

Symbol		Item	Conditions	Ratings	Unit
I_{DRM}		Repetitive Peak Off-State Current, max.	at V_{DRM}, single phase, half wave, Tj = 125°C	10	mA
V_{TM}		Peak On-State Voltage, max.	I_T = 140A Tj = 25°C Inst. measurement	1.55	V
I^+_{GT1}	1	Gate Trigger Current, max.	Tj = 25°C, I_T = 1A, V_D = 6V	200	mA
I^-_{GT1}	2		Tj = 25°C, I_T = 1A, V_D = 6V	200	
I^+_{GT3}	3			–	
I^-_{GT3}	4		Tj = 25°C, I_T = 1A, V_D = 6V	200	
V^+_{GT1}	1	Gate Trigger Voltage, max.	Tj = 25°C, I_T = 1A, V_D = 6V	3	V
V^-_{GT1}	2		Tj = 25°C, I_T = 1A, V_D = 6V	3	
V^+_{GT3}	3			–	
V^-_{GT3}	4		Tj = 25°C, I_T = 1A, V_D = 6V	3	
V_{GD}		Non-Trigger Gate Voltage, min.	Tj = 125°C, V_D = 1/2 V_{DRM}	0.2	V
tgt		Turn On Time, max	I_T = 100A, I_G = 200mA, V_D = 1/2 V_{DRM}, Tj = 25°C dI_G/dt = 1A/μs	10	μs
dv/dt		Critical Rate of Rise of On-State Voltage, min.	Tj = 125°C, V_D = 2/3 V_{DRM}, Exponential wave.	50	V/μs
(dv/dt) c		Critical Rate of Rise off-State Voltage at commutation, min	Tj = 125°C, (di/dt) c = 40A/ms, V_D = 2/3 V_{DRM}	20	V/μs
I_H		Holding Current, typ.	Tj = 25°C	70	mA
$R_{th(j-c)}$		Thermal Impedance, max.	Junction to case	0.3	°C/W

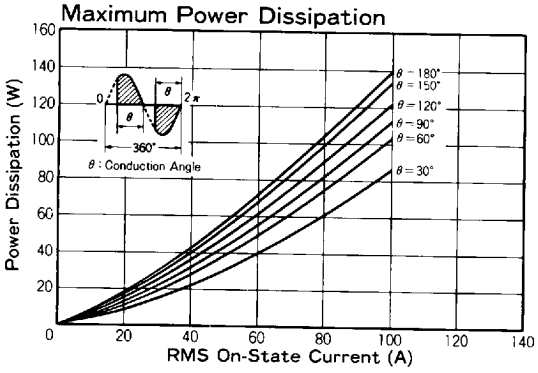
Gate Characteristics



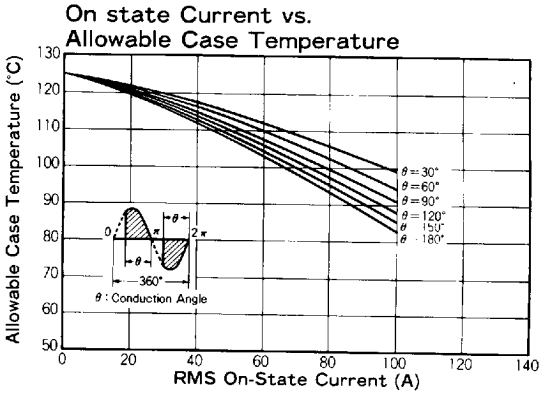
On-state Voltage



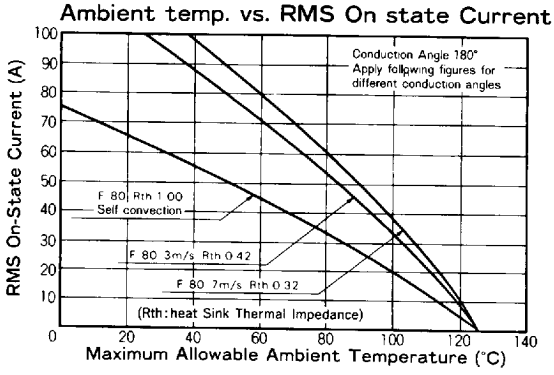
On state Current vs. Maximum Power Dissipation



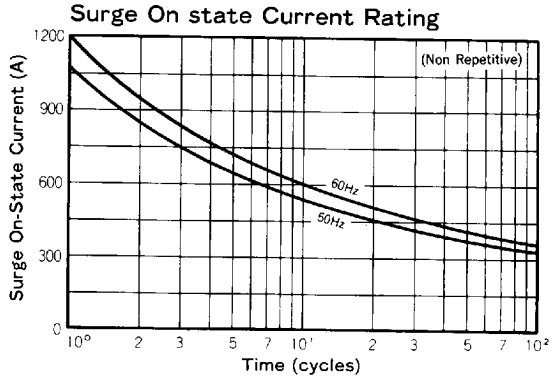
On state Current vs. Allowable Case Temperature



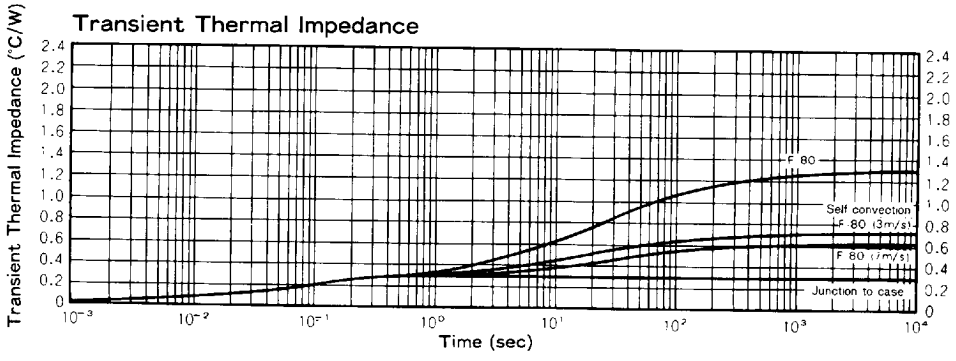
Ambient temp. vs. RMS On state Current



Surge On state Current Rating



Transient Thermal Impedance



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